Docket No.

213480US0

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

Sei TSUNODA, et al.

SERIAL NO:

NEW APPLICATION

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HEREWITH

GAU:

EXAMINER:

FILED: FOR:

LOW DIELECTRIC CONSTANT MATERIAL HAVING THERMAL RESISTANCE, INSULATION FILM BETWEEN SEMICONDUCTOR LAYERS USING THE SAME, AND SEMICONDUCTOR DEVICE

INFORMATION DISCLOSURE/RELATED CASE STATEMENT UNDER 37 CFR 1.97

ASSISTANT COMMISSIONER FOR PATENTS WASHINGTON, D.C. 20231

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application.
 A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- Each item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- □ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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page <u>1</u> of <u>1</u>

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Sei TSUNODA, et al.

SERIAL NO.: New Application

FILED:

Herewith

FOR: LOW DIELECTRIC CONSTANT MATERIAL HAVING THERMAL RESISTANCE,

INSULATION FILM BETWEEN SEMICONDUCTOR LAYERS USING THE SAME, AND

SEMICONDUCTOR DEVICE

STATEMENT OF RELEVANCY

Reference AAA on PTO-1449

This publication disclosed a method for forming an insulation film between layers by using a parylene deposit film or a polyimide film wherein a fluorine atom is incorporated. The publication is cited in the present specification.

However, the publication did not disclose the low dielectric constant film having thermal resistance comprising boron, nitrogen, and hydrogen.

Reference AAB on PTO-1449

This publication disclosed a method for preparing a borazine polymer. The publication is cited in the present specification.

However, the publication did not disclose a low dielectric constant material having thermal resistance, comprising borazine skeletal molecules in an inorganic or organic material molecule.



Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 21348	0US0	SERIAL NO. NEW APPLICATION
LIST ÖF REFERENCES CITED BY APPLICANT		APPLICANT	Sei TSUNODA,	et al.
•		FILING DATE HERE	WITH	GROUP
	OTHER REFERENCES (ncluding Author, Title, I	Date, Pertinent Pages, e	etc.)
AAA	Hideki SHIBATA, "LOW-k INTERLAYER DIELECTRIC TECHNOLOGY FOR HIGH PERFORMANCE LSIs" Technic Survey, Densijyouhoutsuusin Gakkaishi, March 1997, Vol. 80, No. 3, pp. 235-239			
AAB	Yoshihanu KIMURA, "BN FIBER AS A MAIN TOPIC OF INORGANIC FIBERS", Department of Polymer Science and Engineering. Kyoto Institute of Technology, Sennitokogyou, 1996, Vol. 52, No. 8, pp. 341-345			
AAC	R. T. PAINE, et al., "RECENT DEVE Chapter 27, pp. 358-374	LOPMENTS IN BORAZIN	NE-BASED POLYMERS"	, American Chemical Society, 1994,
AAD	P. J. FAZEN, et al. "SYNTHESIS AN Preprints, 1991, Vol. 32, pp. 544-545		ON REACTIONS OF PO	LYBORAZYLENE", Polymer
AAE	C.K. NARULA, et al., "SYNTHESIS O J. Am. Chem. Soc., 1987, Vol. 109, p	OF BORON NITRIDE CER op. 5556-5557	RAMICS FROM POLY (B	ORAZINYLAMINE) PRECURSORS,
AAF	Anne T. LYNCH, et al., "TRANSITION POLYMERIZATIONS, AND CERAMI 1989, Vol. 111, pp. 6201-6209	N-METAL-PROMOTED R C CONVERSION REACT	EACTIONS OF BORON TONS OF B-ALKENYLBO	HYDRIDES. 12.1 SYNTHESES, DRAZINES ", J. Am. Chem. Soc.,
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Examiner			Date Cor	nsidered
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.				